

74AUP1T1326

Low-power dual supply buffer/line driver; 3-state

Rev. 01 — 20 January 2009

Product data sheet

1. General description

The 74AUP1T1326 is a high-performance, low-power, low-voltage, single-bit, dual supply buffer/line driver with output enable circuitry.

The 74AUP1T1326 is designed for logic-level translation applications and combines the functions of the 74AUP1G32 and 74AUP1G126. The buffer/line driver is controlled by two output enable Schmitt trigger inputs (1OE and 2OE) through an OR-gate. The output enable inputs accept standard input signals and are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals. The output of the OR-gate is also available at output 1Y.

The output enable inputs (1OE and 2OE) switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H .

Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 1.1 V and 3.6 V making the device suitable for interfacing between any of the low voltage nodes (1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V) with compatible input levels. Pins 1OE, 2OE and 1Y are referenced to $V_{CC(A)}$ and pins A and 2Y are referenced to $V_{CC(B)}$. A logic LOW on both output enable pins causes the output 2Y to assume a high-impedance OFF-state.

The device ensures low static and dynamic power consumption and is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the outputs, preventing any damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range:
 - ◆ $V_{CC(A)}$: 1.1 V to 3.6 V; $V_{CC(B)}$: 1.1 V to 3.6 V.
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114E Class 2A exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu\text{A}$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V

- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

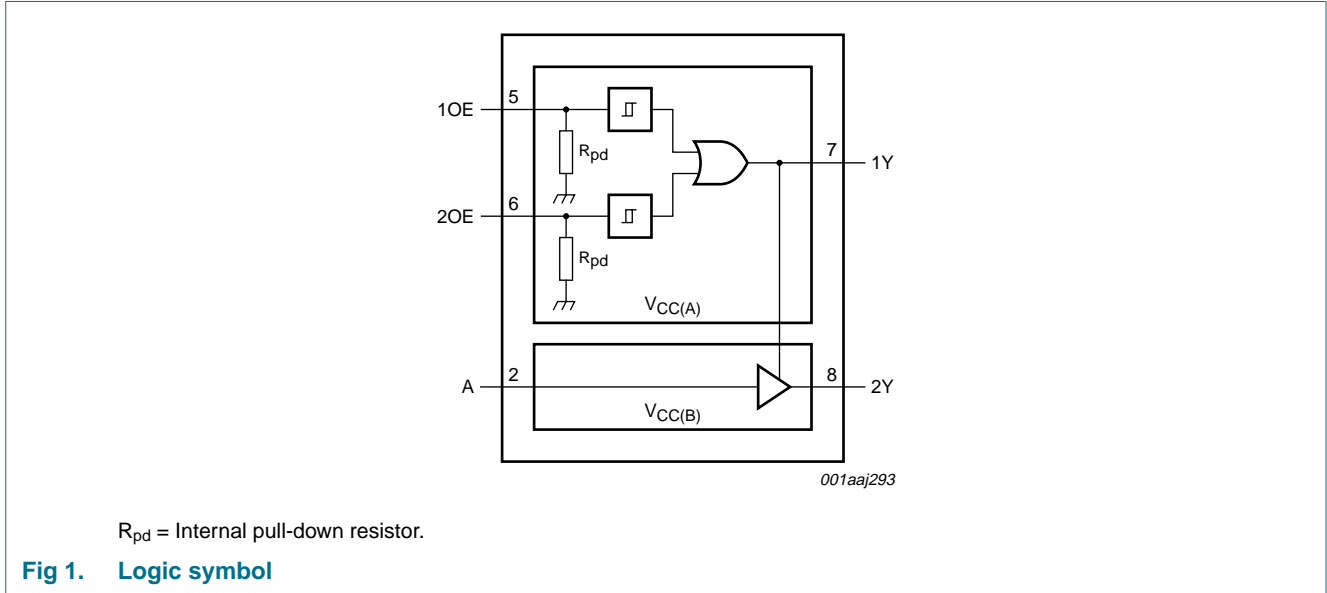
Type number	Package			Version
	Temperature range	Name	Description	
74AUP1T1326GT	$-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm	SOT833-1

4. Marking

Table 2. Marking

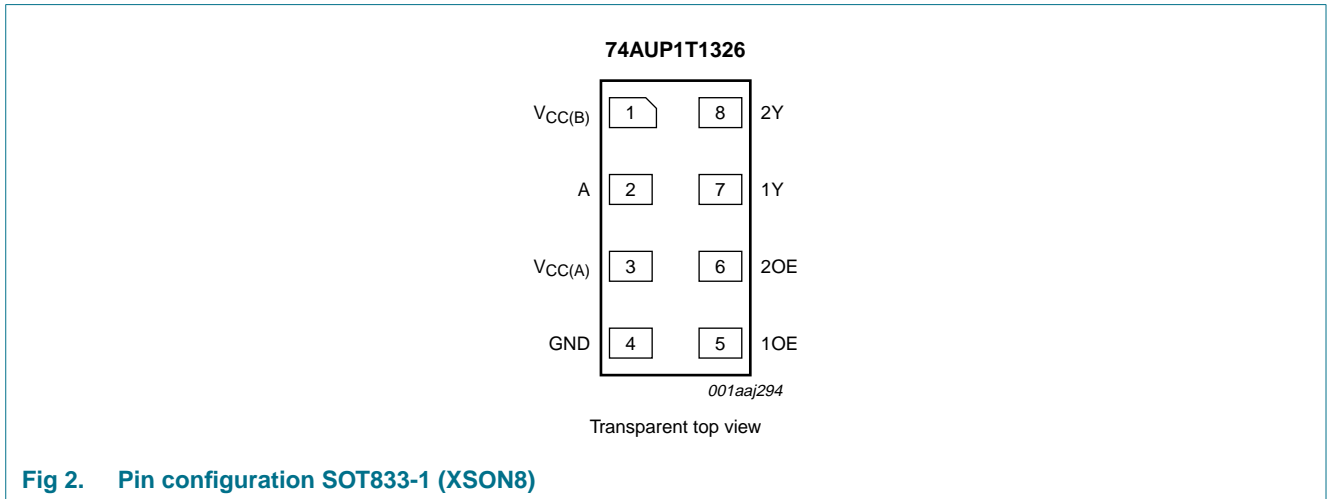
Type number	Marking code
74AUP1T1326GT	p31

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
V _{CC(B)}	1	supply voltage B
A	2	data input
V _{CC(A)}	3	supply voltage A
GND	4	ground (0 V)
1OE	5	output enable input (Schmitt trigger input)
2OE	6	output enable input (Schmitt trigger input)
1Y	7	data output
2Y	8	data output

7. Functional description

Table 4. Function table^[1]

Input			Output	
1OE	2OE	A	1Y	2Y
L	L	X	L	Z
X	H	L	H	L
X	H	H	H	H
H	X	L	H	L
H	X	H	H	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
$V_{CC(B)}$	supply voltage B		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O > V_{CCO}$ or $V_O < 0$ V	[2] -	-50	mA
V_O	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CCO}	[2] -	±20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +85 °C	[3] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with an output pin.

[3] For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.1	3.6	V
$V_{CC(B)}$	supply voltage B		1.1	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage		[1] 0	V_{CCO}	V
T_{amb}	ambient temperature		-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	input A; $V_{CCI} = 1.1$ V to 3.6 V	[2] -	200	ns/V
		input nOE; $V_{CCI} = 1.1$ V to 3.6 V	[2] -	30	ms/V

[1] V_{CCO} is the supply voltage associated with an output pin.

[2] V_{CCI} is the supply voltage associated with an input pin.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ	Max	Min	Max	
T_{amb} = 25 °C								
V _{IH}	HIGH-level input voltage	input A; [1][3]						
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	-	1.6	-	V
		V _{CCI} = 3.0 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	input A; [1][3]						
		V _{CCI} = 1.1 V to 1.95 V	-	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	-	0.9	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IL} or V _I or V _I = V _{T+} or V _{T-}						
		I _O = -20 μA; V _{CCO} = 1.1 V to 3.6 V [2]	V _{CCO} - 0.1	-	-	V _{CCO} - 0.1	-	V
		I _O = -1.1 mA; V _{CCO} = 1.1 V [2]	0.825	-	-	0.825	-	V
		I _O = -1.7 mA; V _{CCO} = 1.4 V	1.05	-	-	1.05	-	V
		I _O = -3 mA; V _{CCO} = 1.65 V	1.2	-	-	1.2	-	V
		I _O = -2.3 mA; V _{CCO} = 2.3 V	1.97	-	-	1.97	-	V
		I _O = -4.0 mA; V _{CCO} = 2.3 V	2.0	-	-	2.0	-	V
		I _O = -2.7 mA; V _{CCO} = 3.0 V	2.67	-	-	2.67	-	V
		I _O = -6.0 mA; V _{CCO} = 3.0 V	2.48	-	-	2.48	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IL} or V _I or V _I = V _{T+} or V _{T-} [2]						
		I _O = 20 μA; V _{CCO} = 1.1 V to 3.6 V	-	-	0.10	-	0.10	V
		I _O = 1.1 mA; V _{CCO} = 1.1 V	-	-	0.275	-	0.275	V
		I _O = 1.7 mA; V _{CCO} = 1.4 V	-	-	0.35	-	0.35	V
		I _O = 3.0 mA; V _{CCO} = 1.65 V	-	-	0.45	-	0.45	V
		I _O = 2.3 mA; V _{CCO} = 2.3 V	-	-	0.33	-	0.33	V
		I _O = 4.0 mA; V _{CCO} = 2.3 V	-	-	0.40	-	0.40	V
		I _O = 2.7 mA; V _{CCO} = 3.0 V	-	-	0.33	-	0.33	V
		I _O = 6.0 mA; V _{CCO} = 3.0 V	-	-	0.40	-	0.40	V
I _I	input leakage current	input A; V _I = 0 V to 3.6 V; V _{CCI} = 1.1 V to 3.6 V [1]	-	-	±0.1	-	±0.5	μA
I _{OZ}	OFF-state output current	output 2Y; V _I = V _{IH} or V _{IL} ; V _O = 0 V to 3.6 V; V _{CC(A)} = 1.1 V to 3.6 V; V _{CC(B)} = 1.1 V to 3.6 V	-	-	±0.1	-	±0.5	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ	Max	Min	Max	
I _{OFF}	power-off leakage current	1Y; V _{CC(A)} = 0 V; V _O = 0 V to 3.6 V; V _{CC(B)} = 1.1 V to 3.6 V	-	-	±0.2	-	±0.5	μA
		A, 2Y; V _{CC(B)} = 0 V; V _I or V _O = 0 V to 3.6 V; V _{CC(A)} = 1.1 V to 3.6 V	-	-	±0.2	-	±0.5	μA
ΔI _{OFF}	additional power-off leakage current	1Y; V _{CC(A)} = 0 V to 0.2 V; V _O = 0 V to 3.6 V; V _{CC(B)} = 1.1 V to 3.6 V	-	-	±0.2	-	±0.6	μA
		A, 2Y; V _{CC(B)} = 0 V to 0.2 V; V _I or V _O = 0 V to 3.6 V; V _{CC(A)} = 1.1 V to 3.6 V	-	-	±0.2	-	±0.6	μA
I _{CC(A)}	supply current A	V _I = 0 V or V _{CC(A)} ; I _O = 0 A [1]	-	-	-	-	-	-
		V _{CC(A)} = 1.1 V to 3.6 V; V _{CC(B)} = 0 V to 3.6 V	-	-	0.5	-	0.9	μA
I _{CC(B)}	supply current B	V _I = 0 V or V _{CC(B)} ; I _O = 0 A [1]	-	-	-	-	-	-
		V _{CC(A)} = V _{CC(B)} = 1.1 V to 3.6 V	-	-	0.5	-	0.9	μA
		V _{CC(A)} = 1.71 V; V _{CC(B)} = 2.6 V	-	-	350	-	500	μA
ΔI _{CC}	additional supply current	nOE; V _{CC(A)} = V _{CC(B)} = 3.3 V; V _I = V _{CC(A)} - 0.6 V	-	-	40	-	50	μA
		A; V _{CC(A)} = V _{CC(B)} = 3.3 V; V _I = V _{CC(B)} - 0.6 V;	-	-	40	-	50	μA
		A; V _I = GND to 3.6 V; nOE = GND; V _{CC(A)} = V _{CC(B)} = 1.1 V to 3.6 V [4]	-	-	-	-	1	μA
R _{pd}	pull-down resistance		151	281	428	150	435	kΩ
C _I	input capacitance	input A; V _I = 0 V or V _{CC(I)} ; V _{CC(I)} = 1.1 V to 3.6 V [1]	-	0.9	-	-	-	pF
		input nOE; V _I = 0 V or V _{CC(I)} ; V _{CC(I)} = 1.1 V to 3.6 V [1]	-	0.8	-	-	-	pF
C _O	output capacitance	1Y; V _O = GND; V _{CCO} = 0 V [2]	-	1.7	-	-	-	pF
		2Y enabled; V _O = GND; V _{CCO} = 0 V [2]	-	1.7	-	-	-	pF
		2Y disabled; V _{CCO} = 0 V to 3.6 V; V _O = GND or V _{CCO} [2]	-	1.5	-	-	-	pF

[1] V_{CC(I)} is the supply voltage associated with the input pin.

[2] V_{CCO} is the supply voltage associated with the output pin.

[3] For V_{CC(I)} values not specified in the data sheet: minimum V_{IH} = 0.7 × V_{CC(I)} and maximum V_{IL} = 0.3 × V_{CC(I)}.

[4] To show I_{CC} remains very low when the input-disable feature is enabled.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit		
			Min	Typ ^[1]	Max	Min	Max			
C_L = 5 pF										
t _{pd}	propagation delay	A to 2Y; see Figure 3	[2]							
		V _{CC(B)} = 1.1 V to 1.3 V	3.0	5.4	9.5	2.7	9.7	ns		
		V _{CC(B)} = 1.4 V to 1.6 V	2.4	3.8	5.7	2.1	6.1	ns		
		V _{CC(B)} = 1.65 V to 1.95 V	1.9	3.1	4.5	1.7	5.0	ns		
		V _{CC(B)} = 2.3 V to 2.7 V	1.5	2.3	3.4	1.3	3.8	ns		
		V _{CC(B)} = 3.0 V to 3.6 V	1.2	2.1	3.0	1.0	3.3	ns		
		nOE to 1Y; see Figure 3	[2]							
		V _{CC(A)} = 1.1 V to 1.3 V	3.4	5.6	9.3	3.2	9.5	ns		
		V _{CC(A)} = 1.4 V to 1.6 V	2.8	4.2	5.9	2.6	6.3	ns		
		V _{CC(A)} = 1.65 V to 1.95 V	2.4	3.5	4.9	2.2	5.3	ns		
		V _{CC(A)} = 2.3 V to 2.7 V	2.2	2.9	3.9	2.0	4.1	ns		
		V _{CC(A)} = 3.0 V to 3.6 V	1.9	2.6	3.4	1.8	3.7	ns		
		C_L = 10 pF								
		t _{pd}	propagation delay	A to 2Y; see Figure 3	[2]					
V _{CC(B)} = 1.1 V to 1.3 V	3.4			6.2	11.0	3.0	11.4	ns		
V _{CC(B)} = 1.4 V to 1.6 V	2.7			4.4	6.6	2.4	7.1	ns		
V _{CC(B)} = 1.65 V to 1.95 V	2.3			3.6	5.3	2.0	5.8	ns		
V _{CC(B)} = 2.3 V to 2.7 V	1.8			2.8	4.1	1.5	4.5	ns		
V _{CC(B)} = 3.0 V to 3.6 V	1.6			2.6	3.8	1.3	4.2	ns		
nOE to 1Y; see Figure 3	[2]									
V _{CC(A)} = 1.1 V to 1.3 V	3.7			6.4	10.8	3.4	11.1	ns		
V _{CC(A)} = 1.4 V to 1.6 V	3.1			4.7	6.8	2.8	7.2	ns		
V _{CC(A)} = 1.65 V to 1.95 V	2.9			4.0	5.6	2.5	6.1	ns		
V _{CC(A)} = 2.3 V to 2.7 V	2.5			3.4	4.6	2.2	4.9	ns		
V _{CC(A)} = 3.0 V to 3.6 V	2.3			3.1	4.1	2.1	4.5	ns		

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit		
			Min	Typ ^[1]	Max	Min	Max			
C_L = 15 pF										
t _{pd}	propagation delay	A to 2Y; see Figure 3	[2]							
		V _{CC(B)} = 1.1 V to 1.3 V	3.8	6.9	12.5	3.4	12.9	ns		
		V _{CC(B)} = 1.4 V to 1.6 V	3.2	4.9	7.5	2.8	8.1	ns		
		V _{CC(B)} = 1.65 V to 1.95 V	2.7	4.0	6.0	2.3	6.5	ns		
		V _{CC(B)} = 2.3 V to 2.7 V	2.2	3.2	4.8	1.8	5.3	ns		
		V _{CC(B)} = 3.0 V to 3.6 V	1.8	2.9	4.4	1.6	4.8	ns		
		nOE to 1Y; see Figure 3	[2]							
		V _{CC(A)} = 1.1 V to 1.3 V	4.2	7.2	12.4	3.8	12.7	ns		
		V _{CC(A)} = 1.4 V to 1.6 V	3.6	5.2	7.6	3.3	8.2	ns		
		V _{CC(A)} = 1.65 V to 1.95 V	3.1	4.5	6.3	2.7	6.9	ns		
		V _{CC(A)} = 2.3 V to 2.7 V	2.8	3.8	5.3	2.5	5.6	ns		
		V _{CC(A)} = 3.0 V to 3.6 V	2.5	3.5	4.8	2.3	5.2	ns		
		C_L = 30 pF								
		t _{pd}	propagation delay	A to 2Y; see Figure 3	[2]					
V _{CC(B)} = 1.1 V to 1.3 V	4.8			9.0	16.6	4.2	17.3	ns		
V _{CC(B)} = 1.4 V to 1.6 V	4.0			6.3	9.8	3.4	10.6	ns		
V _{CC(B)} = 1.65 V to 1.95 V	3.5			5.1	7.8	3.0	8.6	ns		
V _{CC(B)} = 2.3 V to 2.7 V	2.7			4.2	6.2	2.4	6.8	ns		
V _{CC(B)} = 3.0 V to 3.6 V	2.5			3.9	5.9	2.3	6.4	ns		
nOE to 1Y; see Figure 3	[2]									
V _{CC(A)} = 1.1 V to 1.3 V	5.1			9.2	16.4	4.6	17.1	ns		
V _{CC(A)} = 1.4 V to 1.6 V	4.3			6.6	9.9	3.8	10.8	ns		
V _{CC(A)} = 1.65 V to 1.95 V	4.0			5.6	8.1	3.5	8.9	ns		
V _{CC(A)} = 2.3 V to 2.7 V	3.4			4.7	6.7	3.0	7.2	ns		
V _{CC(A)} = 3.0 V to 3.6 V	3.3			4.4	6.2	3.0	6.7	ns		
C_L = 5 pF; V_{CC(A)} = 1.1 V to 1.3 V										
t _{en}	enable time			nOE to 2Y; see Figure 4	[3]					
		V _{CC(B)} = 1.1 V to 1.3 V	3.4	8.7	20.0	3.2	20.3	ns		
		V _{CC(B)} = 1.4 V to 1.6 V	2.8	7.0	15.6	2.5	15.8	ns		
t _{dis}	disable time	nOE to 2Y; see Figure 4	[4]							
		V _{CC(B)} = 1.1 V to 1.3 V	3.4	7.1	15.2	3.2	15.5	ns		
		V _{CC(B)} = 1.4 V to 1.6 V	2.8	6.1	13.5	2.5	13.9	ns		

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
C_L = 5 pF; V_{CC(A)} = 3.0 V to 3.6 V								
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.4	6.5	14.2	3.1	14.4	ns
		V _{CC(B)} = 1.4 V to 1.6 V	2.8	4.8	9.7	2.5	9.9	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.4	4.1	8.2	2.1	8.5	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.2	3.4	6.7	1.9	7.2	ns
		V _{CC(B)} = 3.0 V to 3.6 V	1.9	3.2	6.3	1.6	6.8	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.4	5.3	9.3	3.1	9.7	ns
		V _{CC(B)} = 1.4 V to 1.6 V	2.8	4.3	7.7	2.5	8.0	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.4	4.4	7.4	2.1	7.9	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.2	3.7	6.4	1.9	6.8	ns
		V _{CC(B)} = 3.0 V to 3.6 V	1.9	4.2	6.9	1.6	7.2	ns
C_L = 10 pF; V_{CC(A)} = 1.1 V to 1.3 V								
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	9.9	22.9	3.3	23.1	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	8.0	17.8	2.8	18.1	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	8.5	18.0	3.3	18.3	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	7.3	16.0	2.8	16.4	ns
C_L = 10 pF; V_{CC(A)} = 1.4 V to 1.6 V								
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	8.8	18.8	3.3	19.3	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	6.9	13.8	2.8	14.2	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	6.1	12.2	2.5	12.9	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	7.6	14.0	3.3	14.5	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	6.4	11.9	2.8	12.5	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	6.7	12.0	2.5	12.6	ns
C_L = 10 pF; V_{CC(A)} = 1.65 V to 1.95 V								
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	8.3	17.6	3.3	18.1	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	6.4	12.6	2.8	13.1	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	5.6	11.0	2.5	11.7	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	5.1	9.7	2.2	10.5	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	7.2	12.8	3.3	13.4	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	6.0	10.8	2.8	11.4	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	6.3	10.8	2.5	11.5	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	5.2	9.5	2.2	10.1	ns

C_L = 10 pF; V_{CC(A)} = 2.3 V to 2.7 V

t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	7.7	16.6	3.3	16.9	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	5.8	11.6	2.8	11.9	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	5.0	10.0	2.5	10.5	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	4.4	8.7	2.2	9.3	ns
		V _{CC(B)} = 3.0 V to 3.6 V	2.3	4.3	8.3	2.1	8.8	ns

t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	6.8	11.8	3.3	12.2	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	5.6	9.7	2.8	10.2	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	5.9	9.8	2.5	10.3	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	4.8	8.4	2.2	8.9	ns
		V _{CC(B)} = 3.0 V to 3.6 V	2.3	5.8	9.4	2.1	9.8	ns

C_L = 10 pF; V_{CC(A)} = 3.0 V to 3.6 V

t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	7.4	16.1	3.3	16.5	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	5.5	11.1	2.8	11.5	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	4.7	9.5	2.5	10.1	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	4.1	8.3	2.2	8.8	ns
		V _{CC(B)} = 3.0 V to 3.6 V	2.3	3.9	7.8	2.1	8.3	ns

t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	3.7	6.6	11.3	3.3	11.7	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.1	5.4	9.3	2.8	9.7	ns
		V _{CC(B)} = 1.65 V to 1.95 V	2.9	5.7	9.4	2.5	9.8	ns
		V _{CC(B)} = 2.3 V to 2.7 V	2.5	4.6	8.0	2.2	8.5	ns
		V _{CC(B)} = 3.0 V to 3.6 V	2.3	5.6	9.0	2.1	9.4	ns

C_L = 15 pF; V_{CC(A)} = 1.1 V to 1.3 V

t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	4.2	10.9	25.5	3.8	25.9	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.6	8.9	20.1	3.2	20.6	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	4.2	9.9	20.8	3.8	21.1	ns
		V _{CC(B)} = 1.4 V to 1.6 V	3.6	8.4	18.4	3.2	18.9	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
$C_L = 15 \text{ pF}$; $V_{CC(A)} = 1.4 \text{ V to } 1.6 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	9.7	20.8	3.8	21.4	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	7.6	15.3	3.2	16.1	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	6.8	13.6	2.7	14.5	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	8.9	16.0	3.8	16.6	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	7.4	13.7	3.2	14.4	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	8.0	14.1	2.7	14.8	ns
$C_L = 15 \text{ pF}$; $V_{CC(A)} = 1.65 \text{ V to } 1.95 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	9.1	19.5	3.8	20.1	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	7.0	14.0	3.1	14.7	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	6.2	12.2	2.7	13.2	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	8.5	14.7	3.8	15.3	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	7.0	12.4	3.1	13.1	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	7.5	12.7	2.7	13.5	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	5.6	11.0	2.4	11.8	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	6.1	11.0	2.4	11.8	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	6.1	11.0	2.4	11.8	ns
$C_L = 15 \text{ pF}$; $V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	8.5	18.4	3.8	18.8	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	6.4	13.0	3.2	13.5	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	5.6	11.2	2.7	11.9	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	4.9	10.0	2.5	10.6	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.5	4.8	9.6	2.3	10.1	ns
		$V_{CC(B)} = 3.0 \text{ V to } 3.6 \text{ V}$	2.5	4.8	9.6	2.3	10.1	ns
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	8.0	13.6	3.8	14.0	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	6.6	11.3	3.2	11.8	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	7.1	11.7	2.7	12.3	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	5.7	10.0	2.5	10.5	ns
		$V_{CC(B)} = 3.0 \text{ V to } 3.6 \text{ V}$	2.5	7.1	11.5	2.3	11.9	ns
		$V_{CC(B)} = 3.0 \text{ V to } 3.6 \text{ V}$	2.5	7.1	11.5	2.3	11.9	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
$C_L = 15 \text{ pF}$; $V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	8.2	18.0	3.8	18.4	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	6.1	12.5	3.2	13.0	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	5.2	10.7	2.7	11.5	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	4.6	9.5	2.5	10.1	ns
		$V_{CC(B)} = 3.0 \text{ V to } 3.6 \text{ V}$	2.5	4.4	9.1	2.3	9.6	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	4.2	7.8	13.2	3.8	13.6	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	6.3	10.9	3.2	11.4	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	6.9	11.3	2.7	11.8	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	5.5	9.5	2.5	10.0	ns
		$V_{CC(B)} = 3.0 \text{ V to } 3.6 \text{ V}$	2.5	6.8	11.0	2.3	11.5	ns
$C_L = 30 \text{ pF}$; $V_{CC(A)} = 1.1 \text{ V to } 1.3 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	5.1	13.8	33.1	4.6	33.8	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	4.3	11.2	26.1	3.8	27.7	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	5.1	13.9	28.5	4.6	29.2	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	4.3	11.7	25.4	3.8	26.2	ns
$C_L = 30 \text{ pF}$; $V_{CC(A)} = 1.4 \text{ V to } 1.6 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	5.1	12.1	26.6	4.6	27.5	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	4.3	9.5	19.6	3.8	21.4	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	4.0	8.5	17.7	3.5	19.2	ns
t_{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	5.1	12.6	22.0	4.6	22.9	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	4.3	10.4	18.9	3.8	19.9	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	4.0	11.6	20.1	3.5	21.2	ns
$C_L = 30 \text{ pF}$; $V_{CC(A)} = 1.65 \text{ V to } 1.95 \text{ V}$								
t_{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		$V_{CC(B)} = 1.1 \text{ V to } 1.3 \text{ V}$	5.1	11.4	24.8	4.6	25.6	ns
		$V_{CC(B)} = 1.4 \text{ V to } 1.6 \text{ V}$	4.3	8.7	17.8	3.8	19.5	ns
		$V_{CC(B)} = 1.65 \text{ V to } 1.95 \text{ V}$	4.0	7.7	15.9	3.5	17.3	ns
		$V_{CC(B)} = 2.3 \text{ V to } 2.7 \text{ V}$	3.4	7.1	14.3	3.1	15.3	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

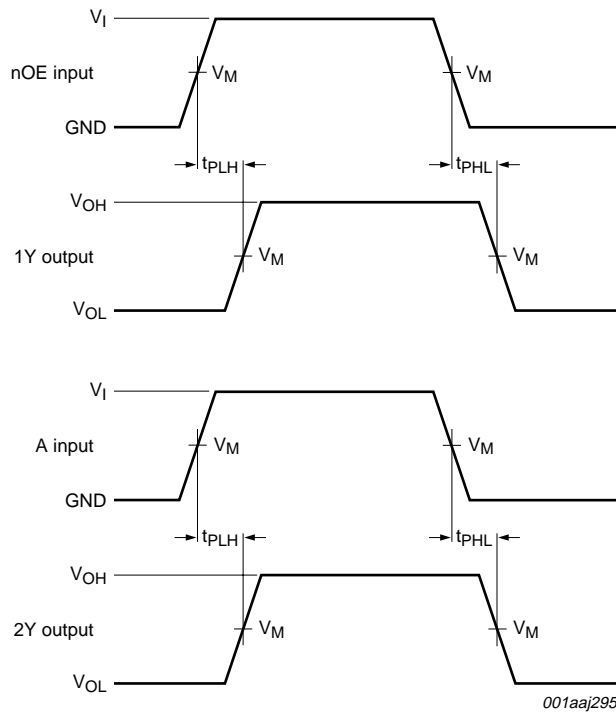
Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	12.0	20.2	4.6	21.0	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	9.9	17.1	3.8	18.0	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	11.1	18.3	3.5	19.3	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	8.7	15.5	3.2	16.4	ns
C_L = 30 pF; V_{CC(A)} = 2.3 V to 2.7 V								
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	10.6	23.3	4.6	23.9	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	7.9	16.4	3.8	17.8	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	6.9	14.4	3.5	15.6	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	6.2	12.8	3.2	13.6	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	11.5	18.7	4.6	19.3	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	9.3	15.6	3.8	16.3	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	10.5	16.8	3.5	17.5	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	8.2	14.0	3.2	14.7	ns
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	10.2	22.9	4.6	23.4	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	7.6	15.9	3.8	17.2	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	6.6	14.0	3.5	15.1	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	5.8	12.4	3.2	13.1	ns
t _{dis}	disable time	nOE to 2Y; see Figure 4 ^[4]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	11.2	18.3	4.6	18.8	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	9.1	15.2	3.8	15.8	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	10.2	16.4	3.5	17.0	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	7.9	13.6	3.2	14.2	ns
t _{en}	enable time	nOE to 2Y; see Figure 4 ^[3]						
		V _{CC(B)} = 1.1 V to 1.3 V	5.1	10.5	16.5	3.1	17.1	ns
		V _{CC(B)} = 1.4 V to 1.6 V	4.3	9.1	15.2	3.8	15.8	ns
		V _{CC(B)} = 1.65 V to 1.95 V	4.0	10.2	16.4	3.5	17.0	ns
		V _{CC(B)} = 2.3 V to 2.7 V	3.4	7.9	13.6	3.2	14.2	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
C_L = 5 pF, 10 pF, 15 pF and 30 pF								
C _{PD}	power dissipation capacitance	output 2Y; f _i = 1 MHz; V _I = 0 V to V _{CC} ^[5]						
		V _{CC(A)} = V _{CC(B)} = 1.2 V	-	2.8	-	-	-	pF
		V _{CC(A)} = V _{CC(B)} = 1.5 V	-	3.0	-	-	-	pF
		V _{CC(A)} = V _{CC(B)} = 1.8 V	-	3.0	-	-	-	pF
		V _{CC(A)} = V _{CC(B)} = 2.5 V	-	3.6	-	-	-	pF
		V _{CC(A)} = V _{CC(B)} = 3.3 V	-	4.1	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC(A)} and V_{CC(B)}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] t_{en} is the same as t_{PZH} and t_{PZL}.
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ}.
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

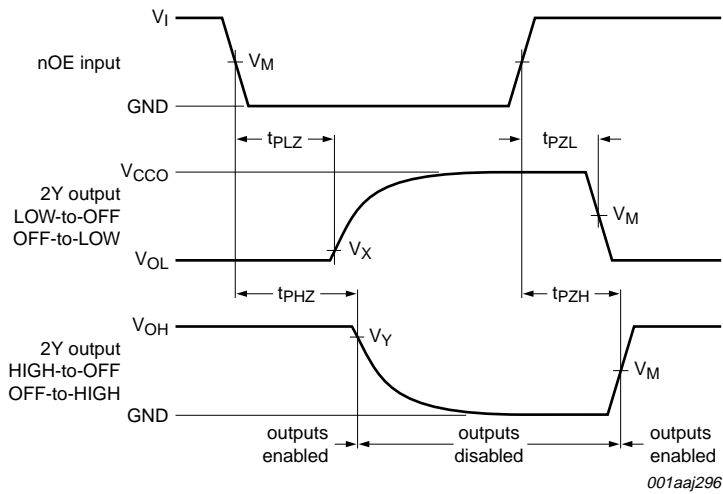
12. Waveforms



Measurement points are given in [Table 9](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 3. Input nOE to output 1Y and A to output 2Y propagation delay times



Measurement points are given in [Table 9](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.
 V_{CC0} is the supply voltage associated with the output pin.
 Output 1Y has no external load.

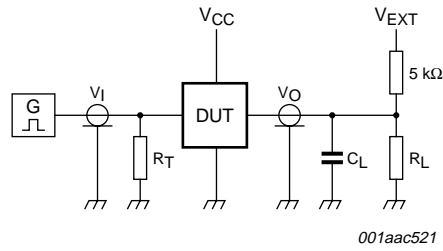
Fig 4. Enable and disable times

Table 9. Measurement points

Supply voltage	Input ^[1]	Output ^[2]		
$V_{CC(A)}, V_{CC(B)}$	V_M	V_M	V_X	V_Y
1.1 V to 1.6 V	$0.5V_{CCI}$	$0.5V_{CC0}$	$V_{OL} + 0.1\text{ V}$	$V_{OH} - 0.1\text{ V}$
1.65 V to 2.7 V	$0.5V_{CCI}$	$0.5V_{CC0}$	$V_{OL} + 0.15\text{ V}$	$V_{OH} - 0.15\text{ V}$
3.0 V to 3.6 V	$0.5V_{CCI}$	$0.5V_{CC0}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CC0} is the supply voltage associated with the output port.



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 5. Load circuit for switching times

Table 10. Test data

Supply voltage	Input		Load ^[2]		V_{EXT}		
$V_{CC(A)}, V_{CC(B)}$	V_I ^[1]	$t_r = t_f$	C_L	R_L ^[3]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ} ^[4]
1.1 V to 3.6 V	V_{CCI}	≤ 3.0 ns	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2V_{CCO}$

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] For measuring enable and disable times, C_L and R_L are connected to pin 2Y. Pin 1Y has no load.

[3] For measuring enable and disable times $R_L = 5$ kΩ, for measuring propagation delays $R_L = 1$ MΩ.

[4] V_{CCO} is the supply voltage associated with the output port.

13. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 5](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit
			Min	Typ	Max	Min	Max	
V _{T+}	positive-going threshold voltage	nOE inputs; see Figure 6 and Figure 7						
		V _{CC(A)} = 1.1 V	0.53	-	0.90	0.53	0.90	V
		V _{CC(A)} = 1.4 V	0.74	-	1.11	0.74	1.11	V
		V _{CC(A)} = 1.65 V	0.91	-	1.29	0.91	1.29	V
		V _{CC(A)} = 2.3 V	1.37	-	1.77	1.37	1.77	V
		V _{CC(A)} = 3.0 V	1.88	-	2.29	1.88	2.29	V
V _{T-}	negative-going threshold voltage	nOE inputs; see Figure 6 and Figure 7						
		V _{CC(A)} = 1.1 V	0.26	-	0.65	0.26	0.65	V
		V _{CC(A)} = 1.4 V	0.39	-	0.75	0.39	0.75	V
		V _{CC(A)} = 1.65 V	0.47	-	0.84	0.47	0.84	V
		V _{CC(A)} = 2.3 V	0.69	-	1.04	0.69	1.04	V
		V _{CC(A)} = 3.0 V	0.88	-	1.24	0.88	1.24	V
V _H	hysteresis voltage	nOE inputs; (V _{T+} - V _{T-}); see Figure 6 , Figure 7 , Figure 8 and Figure 9						
		V _{CC(A)} = 1.1 V	0.08	-	0.46	0.08	0.46	V
		V _{CC(A)} = 1.4 V	0.18	-	0.56	0.18	0.56	V
		V _{CC(A)} = 1.65 V	0.27	-	0.66	0.27	0.66	V
		V _{CC(A)} = 2.3 V	0.53	-	0.92	0.53	0.92	V
		V _{CC(A)} = 3.0 V	0.79	-	1.31	0.79	1.31	V

14. Waveforms transfer characteristics

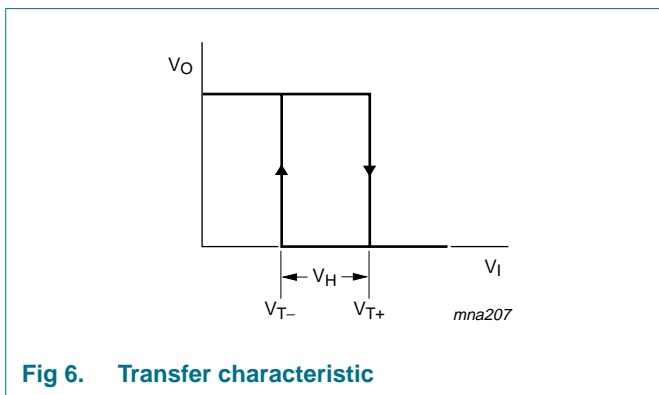


Fig 6. Transfer characteristic

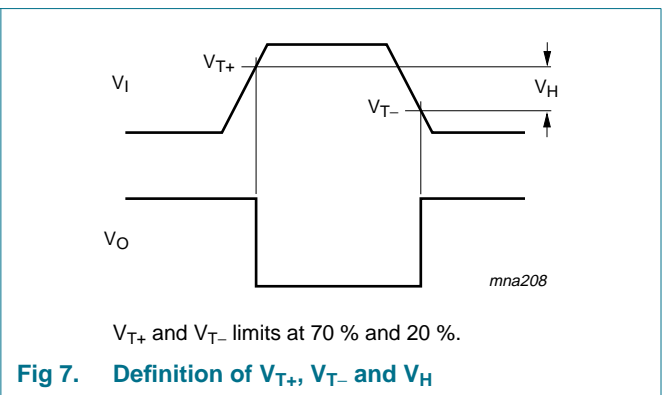


Fig 7. Definition of V_{T+}, V_{T-} and V_H

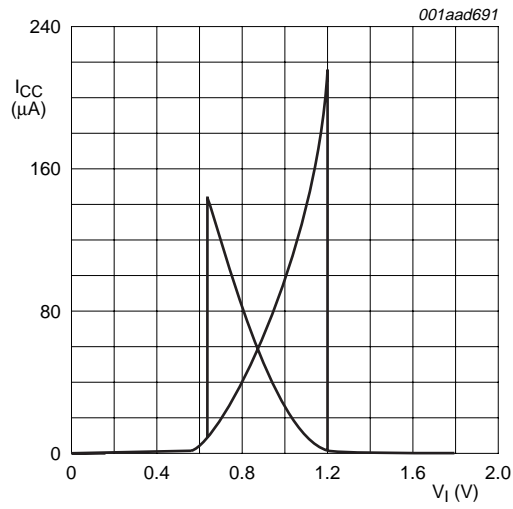


Fig 8. Typical transfer characteristics; $V_{CC(A)} = 1.8$ V

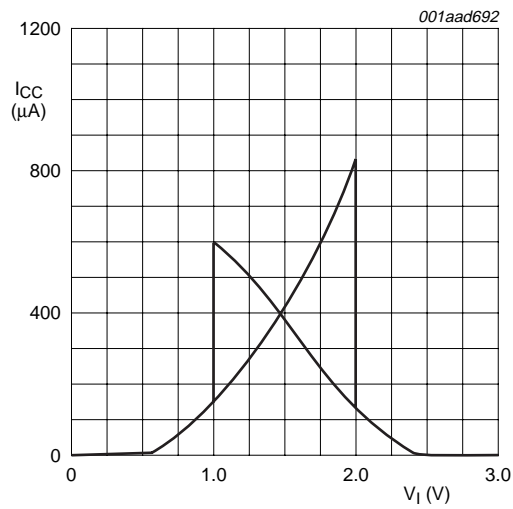


Fig 9. Typical transfer characteristics; $V_{CC(A)} = 3.0$ V

15. Package outline

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

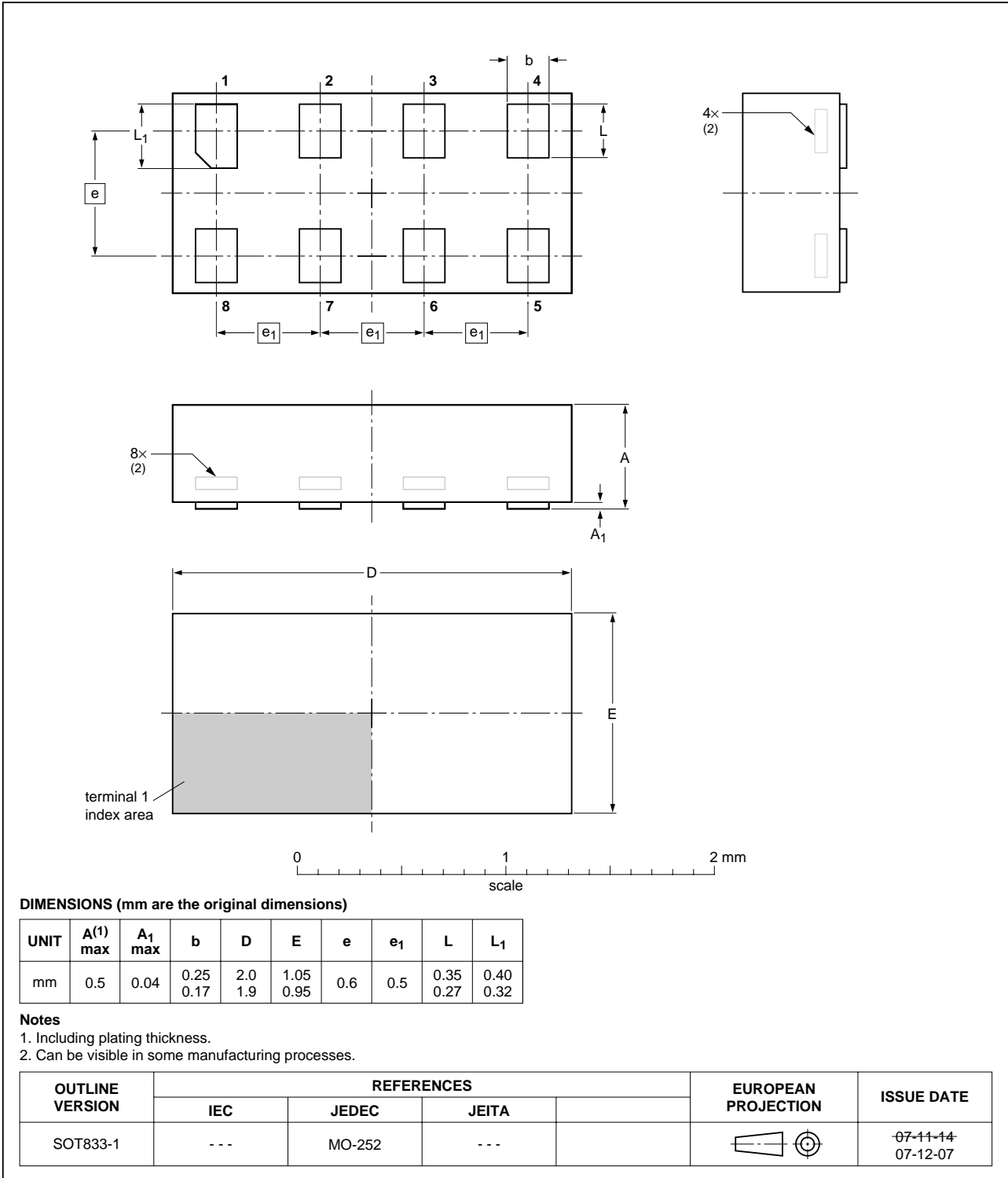


Fig 10. Package outline SOT833-1 (XSON8)

16. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

17. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T1326_1	20090120	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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